SK 35 BZ



SEMITOP® 2

1-phase bridge rectifier with one diode arm and one thyristor arm SK 35 BZ

Target Data

Features

- Compact design
- · One screw mounting
- · Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DBC)
- Glass passivated thyristor chipsReverse voltage up to 1600 V
- High surge currents

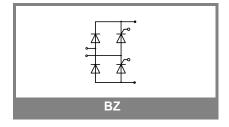
Typical Applications*

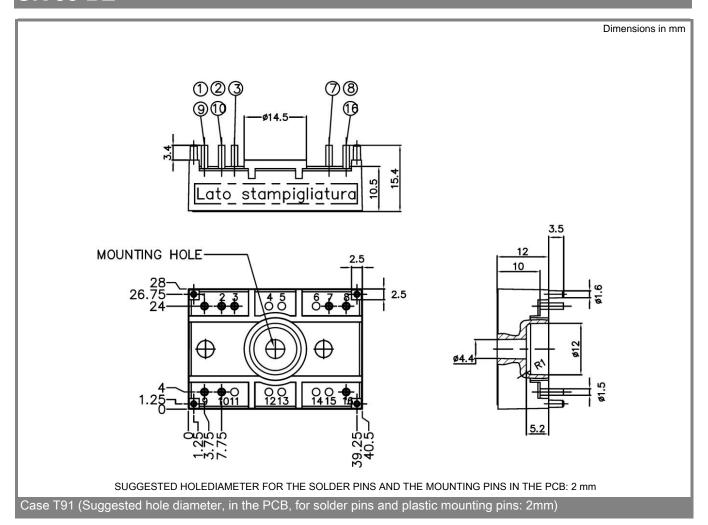
Field regulator

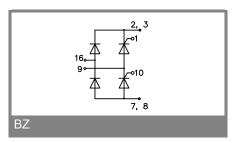
1) V_F , V_T , $V_{(TO)}$, $V_{T(TO)}$, r_{diode} , r_{hty} = chip level

V_{RSM}	V_{RRM}, V_{DRM}	I _F = 35 A
V	V	(T _s = 80 °C)
900	800	SK35BZ08
1300	1200	SK35BZ12
1700	1600	SK35BZ16

Characte	ristics	$T_{s} = 25$	5°C unless otherwise	specified
Symbol	Conditions		Values	Units
I _F	T _s = 80°C per diode		35	Α
I_{T}	T _s = 80°C per thyristor		25	Α
I _{FAV}	sin. 180°; T _s = 25 (80) °C per diode		35 (25)	А
I _{TSM} /I _{FSM}	T _{vj} = 25 (125) °C; 10 ms		370 (270)	А
I²t	T _{vj} = 25 (125) °C; 8,3 10 ms		685 (365)	A²s
T _{stg}			-40,+125	°C
T _{solder}	terminals, 10 s		260	°C
Thyristor	•			
(dv/dt) _{cr}	T _{vj} = 125 °C		1000	V/µs
(di/dt) _{cr}	T _{vj} = 125 °C; f = f = 50 60 Hz		50	A/μs
t_q	$T_{vj} = 125 ^{\circ}\text{C}; \text{ typ.}$		150	μs
I _H	T _{vj} = 25 °C; typ. / max.		80 / 165	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω ; typ. / max.		150 / 330	mA
V _T	T_{vj} = 125 °C; (I_T = 25 A); max.		1,2	V
$V_{T(TO)}$	T _{vj} = 125 °C		max. 0,85	V
r _T	T _{vi} = 125 °C		max. 14	mΩ
I_{DD} ; I_{RD}	T_{vj}^{s} = 125 °C; $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$		max. 8	mA
$R_{th(j-s)}$	Cont. per thyristor		1,7	K/W
T _{vi}			- 40 + 125	°C
V _{GT}	T_{vj} = 25 °C; d.c.		2	V
I_{GT}	T _{vi} = 25 °C; d.c.		100	mA
V_{GD}	$T_{vi} = 125 ^{\circ}\text{C}; \text{d.c.}$		0,25	V
I_{GD}	T _{vj} = 125 °C; d.c.		3	mA
Diode				
V_{F}	T_{vi} = 125 °C; (I_F = 15 A); max.		1,1	V
$V_{(TO)}$	T _{vi} = 125 °C		0,83	V
r _T	T _{vj} = 125 °C		13	mΩ
I_{RD}	$T_{vj} = 150 ^{\circ}\text{C}; V_{RD} = V_{RRM}$		4	mA
R _{th(j-s)}	per diode		1,7	K/W
T_{vj}			-40+150	°C
Mechanic	cal data			•
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min		3000 (2500)	V
M ₁	mounting torque		2	Nm
w			19	g
Case	SEMITOP® 2		T 91	







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.